



BIPOLAR TRANSISTOR MODULES

Ratings and Specifications

30 1400 volts class power transistor modules

- Power transistors and free wheel diodes are built into one package.
- Terminal layout in which drive wiring and power wiring do not come accross.

Device type	V _{CB0}	V _{CE0}	V _{CEX} (sus)	I _C cont.	P _C	h _{FE} min.	V _{CE}		Switching time (Max.)			Package	Net mass Grams	Equivalent circuit Page 32, 33
	Volts	Volts	Volts	Amps.	Watts		I _C Amps.	Volts	t _{on} μsec.	t _{stg} μsec.	t _r μsec.			
2DI30A-140	1400	1400	1200	30	300	70	30	5	3.0	15	3	M204	175	Fig. E1
2DI100A-140	1400	1400	1200	100	800	70	100	5	3.0	15	3	M207	550	Fig. E2
1DI200A-140	1400	1400	1200	200	1400	70	200	5	3.0	15	3	M105	560	Fig. D1

31 6 in one-package power transistor modules

- 6 power transistors and 6 free wheel diodes are built into one package.
- Terminal layout in which drive wiring and power wiring do not come accross.

Device type	V _{CB0}	V _{CE0}	V _{CEX} (sus)	I _C cont.	P _C	h _{FE} min.	V _{CE}		Switching time (Max.)			Package	Net mass Grams	Equivalent circuit Page 34, 35
	Volts	Volts	Volts	Amps.	Watts		I _C Amps.	Volts	t _{on} μsec.	t _{stg} μsec.	t _r μsec.			
6DI10A-050	600	600	450	10	80	100	10	5	1.0	12	2	M601	130	Fig. H1
EVF31T-050A	600	600	450	15	100	100	15	5	1.0	15	2.5	M602	180	Fig. H1
6DI15A-050	600	600	450	15	80	100	15	5	1.0	12	2	M604	150	Fig. H1
6DI20C-050	600	600	450	20	120	100	20	5	1.0	12	2	M604	150	Fig. H1
6DI30A-050	600	600	450	30	150	100	30	5	1.5	12	3	M603	450	Fig. H2
6DI30B-050	600	600	450	30	200	100	30	5	1.0	12	2	M605	210	Fig. H3
6DI50B-050	600	600	450	50	230	100	50	5	3.0	12	4	M606	450	Fig. H3
6DI50C-050	600	600	450	50	230	100	50	5	1.5	12	3	M603	450	Fig. H2
6DI75A-050	600	600	450	75	350	100	75	5	1.5	12	3	M603	450	Fig. H2
6DI100A-050	600	600	450	100	400	80	100	5	3.0	15	4	M603	450	Fig. H2
6DI10A-120	1200	1200	1200	10	100	70	10	5	3.0	15	3	M604	150	Fig. J2
6DI15A-120	1200	1200	1200 *	15	150	70	15	5	3.0	15	3	M605	210	Fig. J1
6DI30A-120	1200	1200	1200 *	30	230	70	30	5	3.0	15	3	M606	450	Fig. J1

* V_{CEX} (sus)

32 Low voltage high current power transistor modules

- Terminal layout in which drive wiring and power wiring do not come accross.
- Power transistors and free wheel diodes are built into one package.

Device type	V _{CB0}	V _{CE0}	V _{CEX} (sus)	I _C cont.	P _C	h _{FE} min.	V _{CE}		Switching time (Max.)			Package	Net mass Grams	Equivalent circuit Page 32
	Volts	Volts	Volts	Amps.	Watts		I _C Amps.	Volts	t _{on} μsec.	t _{stg} μsec.	t _r μsec.			
2DI200A-020	300	300	250	200	500	100	200	5	2.0	12	3	M203	450	Fig. C4